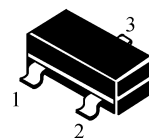


SOT-23

- 1. BASE
- 2. EMITTER
- 3. COLLECTOR



## ■ MAXIMUM RATINGS (T<sub>a</sub>=25°C) 最大額定值

Characteristic 特性參數	Symbol 符號	Rating 額定值	Unit 單位
Collector-Base Voltage 集電極-基極電壓	V <sub>CBO</sub>	-30	V
Collector-Emitter Voltage 集電極-發射極電壓	V <sub>CEO</sub>	-25	V
Emitter-Base Voltage 發射極-基極電壓	V <sub>EBO</sub>	-5	V
Collector Current-Continuous 集電極電流-連續	I <sub>c</sub>	-700	mA
Collector Power Dissipation 集電極耗散功率	P <sub>C</sub>	225	mW
Junction Temperature 結溫	T <sub>j</sub>	150	°C
Storage Temperature Range 儲存溫度	T <sub>stg</sub>	-55~150	°C

## ■ DEVICE MARKING 打標

B624(2SB624)					
MARK	BV1	BV2	BV3	BV4	BV5
H <sub>FE1</sub>	110~180	135~220	170~270	200~320	250~400



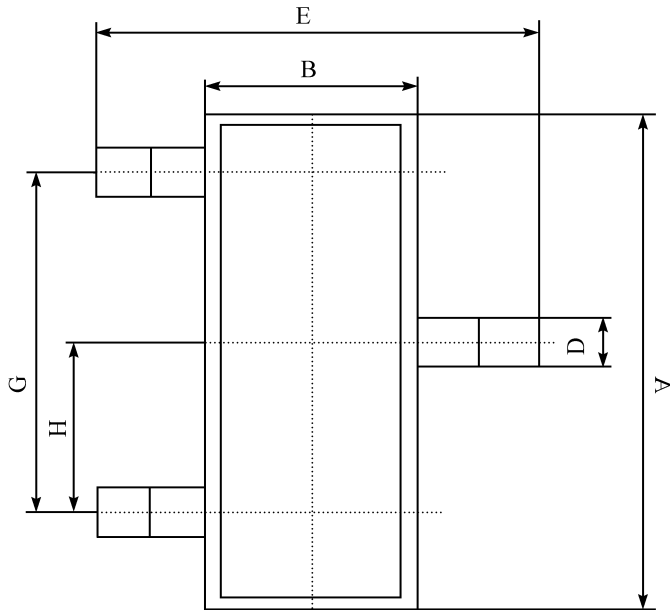
B624

**■ELECTRICAL CHARACTERISTICS 電特性**

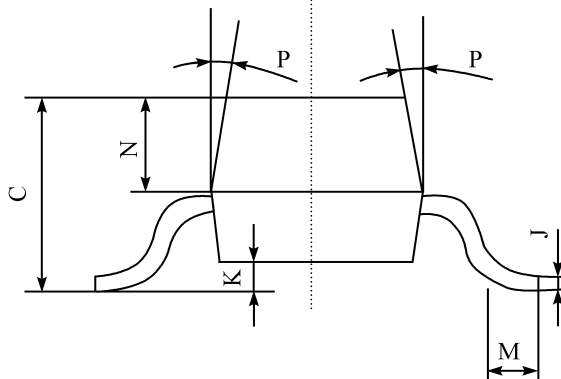
(T<sub>A</sub>=25°C unless otherwise noted 如無特殊說明,溫度為 25°C)

Characteristic 特性參數	Symbol 符號	Test Condition 測試條件	Min 最小值	Typ 典型值	Max 最大值	Unit 單位
Collector Cutoff Current 集電極截止電流	I <sub>CBO</sub>	V <sub>CB</sub> =-30V, I <sub>E</sub> =0	—	—	-0.1	μA
Emitter Cutoff Current 發射極截止電流	I <sub>EBO</sub>	V <sub>EB</sub> =-5V, I <sub>C</sub> =0	—	—	-0.1	μA
Collector-Base Breakdown Voltage 集電極-基極擊穿電壓	V <sub>(BR)CBO</sub>	I <sub>C</sub> =-100 μA	-30	—	—	V
Collector-Emitter Breakdown Voltage 集電極-發射極擊穿電壓	V <sub>(BR)CEO</sub>	I <sub>C</sub> =-1.0mA	-25	—	—	V
Emitter-Base Breakdown Voltage 發射極-基極擊穿電壓	V <sub>(BR)EBO</sub>	I <sub>E</sub> =-100 μA	-5	—	—	V
DC Current Gain 直流電流增益	H <sub>FE1</sub>	V <sub>CE</sub> =-1V, I <sub>C</sub> =-100mA	110	200	400	—
DC Current Gain 直流電流增益	H <sub>FE2</sub>	V <sub>CE</sub> =-1V, I <sub>C</sub> =-700mA	50	—	—	—
Collector-Emitter Saturation Voltage 集電極-發射極飽和壓降	V <sub>CE(sat)</sub>	I <sub>C</sub> =-700mA, I <sub>B</sub> =-70mA	—	-0.25	-0.6	V
Base-Emitter Saturation 基極-發射極電壓	V <sub>BE</sub>	V <sub>CE</sub> =-6V, I <sub>C</sub> =-10mA	-0.6	-0.64	-0.7	V
Transition Frequency 特徵頻率	f <sub>T</sub>	V <sub>CE</sub> =-6V, I <sub>C</sub> =-10mA	—	160	—	MHz
Collector Output Capacitance 輸出電容	C <sub>ob</sub>	V <sub>CB</sub> =-6V, I <sub>E</sub> =0, f=1MHz	—	17	—	pF

## ■DIMENSION 外形封裝尺寸



序號	數值及公差
A	$2.90 \pm 0.10$
B	$1.30 \pm 0.10$
C	$1.00 \pm 0.10$
D	$0.40 \pm 0.10$
E	$2.40 \pm 0.20$
G	$1.90 \pm 0.10$
H	$0.95 \pm 0.05$
J	$0.13 \pm 0.05$
K	$0.00-0.10$
M	$\geq 0.2$
N	$0.60 \pm 0.10$
P	$7 \pm 2^\circ$



This datasheet presents technical data of Tak Cheong's Silicon Rectifier Diodes. Complete specifications for the individual devices are provided in the form of datasheets. A comprehensive Selector Guide is included to simplify the task of choosing the best set of components required for a specific application. For additional information, please visit our website <http://www.takcheong.com>.

Although information in this datasheet has been carefully checked, no responsibility for the inaccuracies can be assumed by Tak Cheong. Please consult your nearest Tak Cheong's sales office for further assistance.

Tak Cheong reserves the right to make changes without further notice to any products herein to further improve reliability, function or design, cost and productivity.

**KEL<sup>®</sup>** is registered trademarks of Tak Cheong Electronics (Holdings) Co., Ltd.